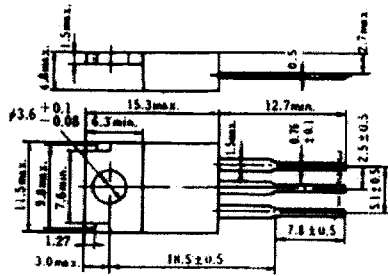


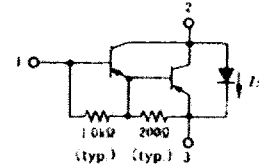
2SB955 (K)

SILICON PNP TRIPLE DIFFUSED
POWER SWITCHING
COMPLEMENTARY PAIR WITH 2SD1126(K)



(JEDEC TO-220AB)

1. Base
 2. Collector (Flange)
 3. Emitter
- (Dimensions in mm)



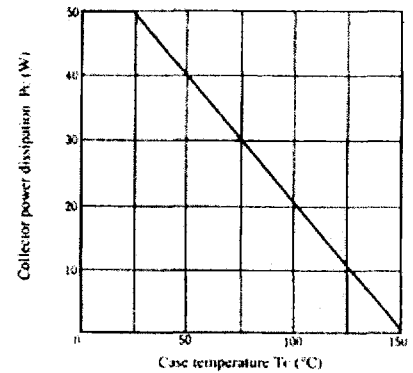
■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB955(K)	Unit
Collector to base voltage	V _{CB0}	-120	V
Collector to emitter voltage	V _{CE0}	-120	V
Emitter to base voltage	V _{EB0}	-7	V
Collector current	I _C	-10	A
Collector peak current	i _{C(peak)}	-15	A
C to E diode forward current	I _D *	10	A
Collector power dissipation	P _C *	50	W
Junction temperature	T _J	150	°C
Storage temperature	T _{sig}	-55 to +150	°C

* Value at T_c = 25°C

** P_W ≤ 1ms 1shot

MAXIMUM COLLECTOR DISSIPATION CURVE



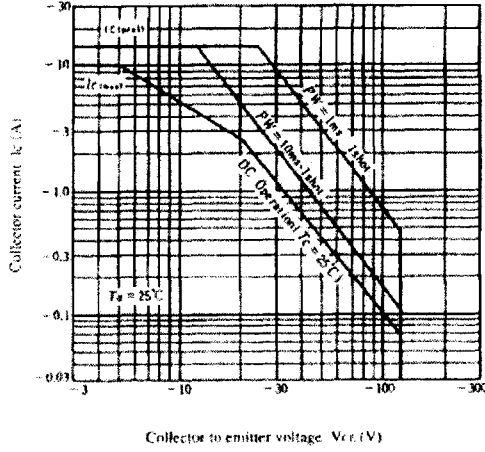
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V _{BR(CEO)}	I _C = -25mA, R _{BE} = ∞	-120	—	—	V
Emitter to base breakdown voltage	V _{BR(EB0)}	I _E = -200mA, I _C = 0	-7	—	—	V
Collector cutoff current	I _{CB0}	V _{CB} = -120V, I _E = 0	—	—	-100	μA
	I _{CE0}	V _{CE} = -100V, R _{BE} = ∞	—	—	-10	μA
DC current transfer ratio	h _{FE}	V _{CE} = -3V, I _C = -5A*	1000	—	20000	
Collector to emitter saturation voltage	V _{CE(sat)1}	I _C = -5A, I _B = -10mA*	—	—	-1.5	V
	V _{CE(sat)2}	I _C = -10A, I _B = -0.1A*	—	—	-3.0	V
Base to emitter saturation voltage	V _{BE(sat)1}	I _C = -5A, I _B = -10mA*	—	—	-2.0	V
	V _{BE(sat)2}	I _C = -10A, I _B = -0.1A*	—	—	-3.5	V
C to E diode forward voltage	V _D	I _D = 10A*	—	—	3.0	V
Turn on time	t _{on}	V _{CC} = -30V	—	0.8	—	μs
Turn off time	t _{off}	I _C = -5A, I _{B1} = -I _{B2} = -10mA	—	4.0	—	μs

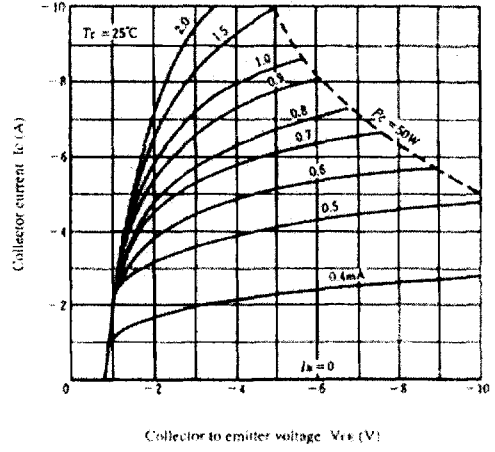
* Pulse Test

2SB955K

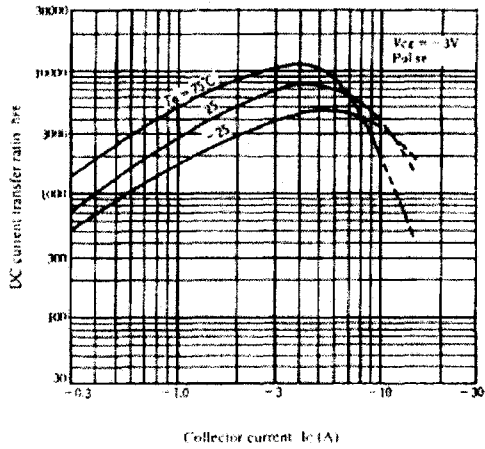
AREA OF SAFE OPERATION



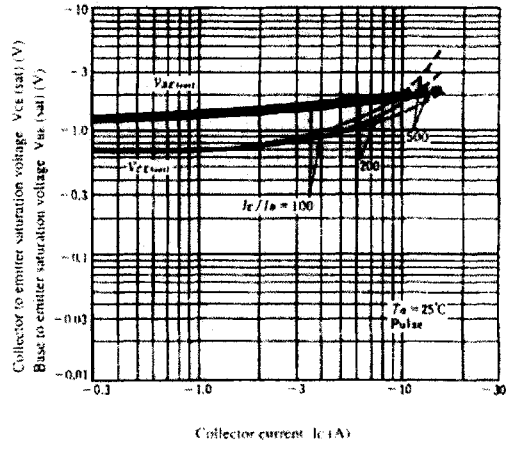
TYPICAL OUTPUT CHARACTERISTICS



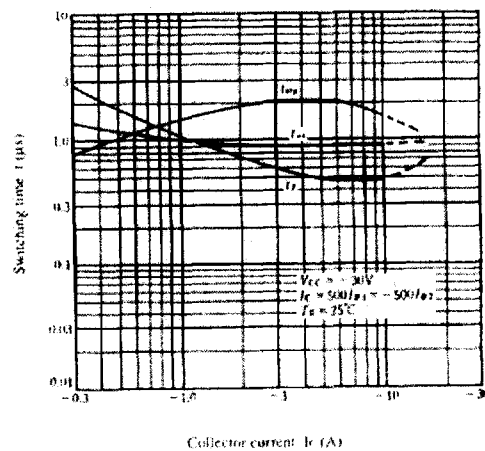
DC CURRENT TRANSFER RATIO VS COLLECTOR CURRENT



SATURATION VOLTAGE VS COLLECTOR CURRENT



SWITCHING TIME VS COLLECTOR CURRENT



DIODE CURRENT VS FORWARD VOLTAGE

